N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	20V
I_D	3.0A
$R_{DS(ON)}$(at V_{GS}=4.5V)	50 mohm
$R_{DS(ON)}$(at V_{GS}=2.5V)	70 mohm

Electrical Characteristics (T_J=25 unless otherwise noted)

Typical Performance Characteristics

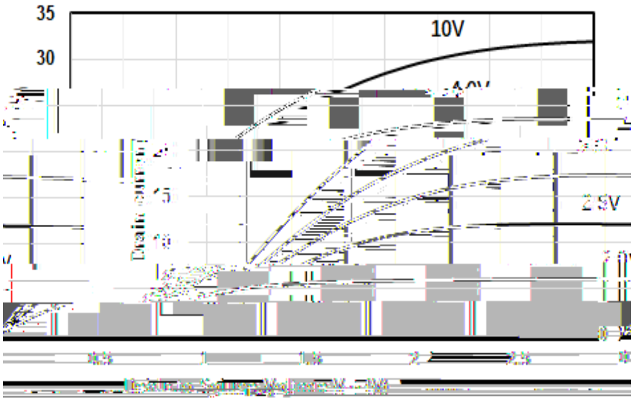


Figure1. Output Characteristics

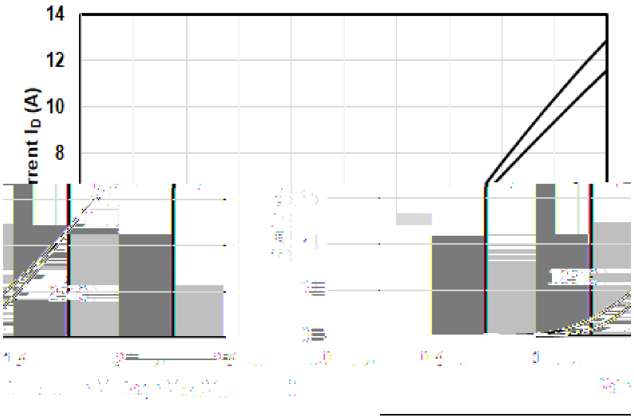


Figure2. Transfer Characteristics

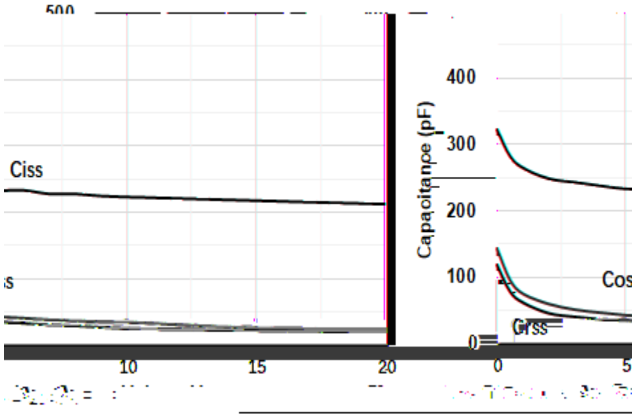


Figure3. Capacitance Characteristics

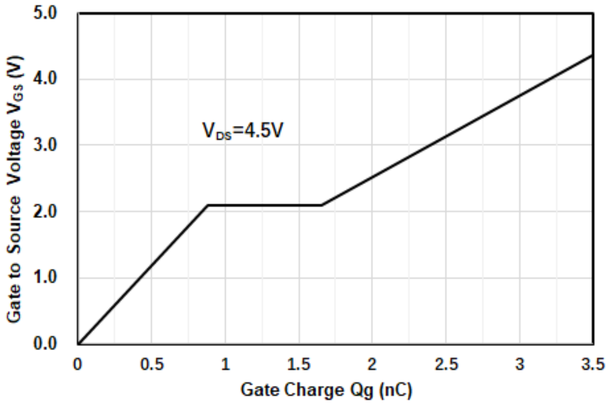


Figure4. Gate Charge

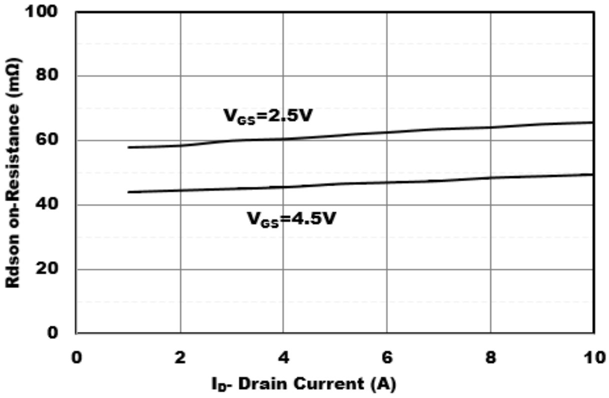


Figure5. Drain-Source on Resistance

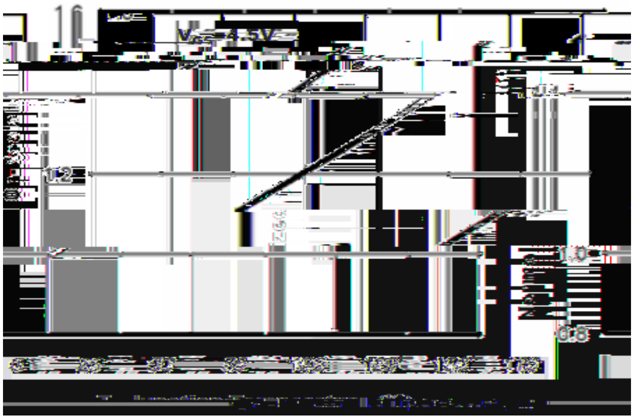


Figure6. Drain-Source on Resistance

[redacted]

Figure7. Safe Operation Area

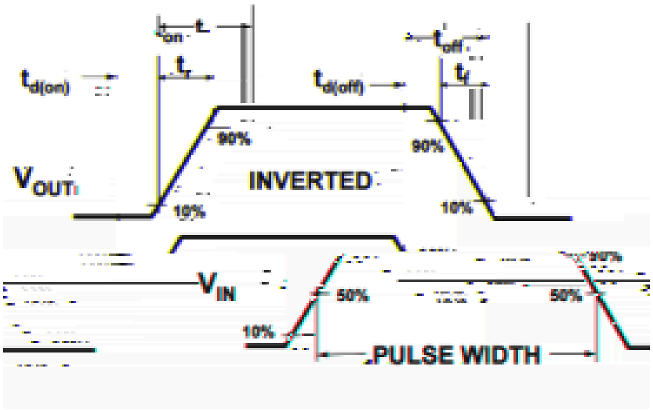


Figure8. Switching wave

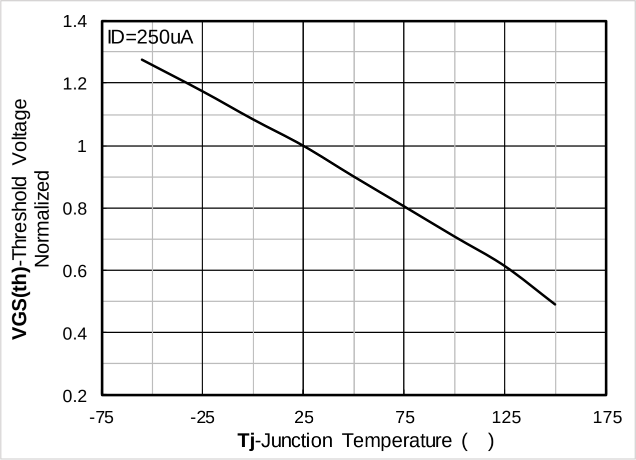


Figure 9. Normalized Threshold voltage

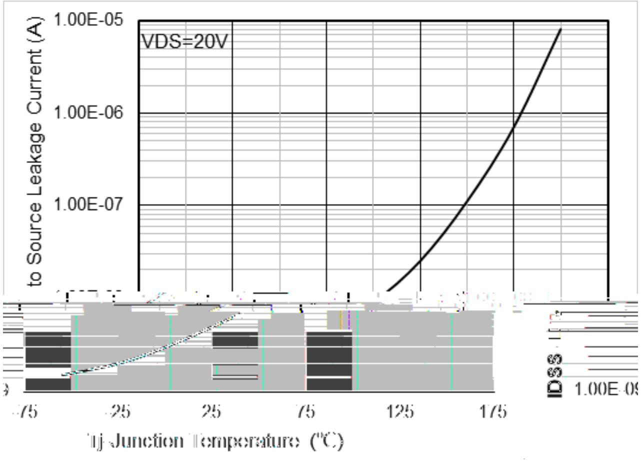
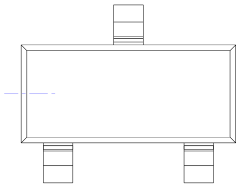
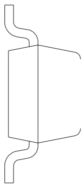
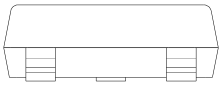


Figure 10. Drain to Source Leakage Current

SOT-23 Package information







UNIT mm